STELLA MARIS COLLEGE (AUTONOMOUS) CHENNAI – 600 086.

(For candidates admitted during the academic year 2004-05 & thereafter)

SUBJECT CODE: PH/MC/ES54

B.Sc. DEGREE EXAMINATION NOVEMBER 2008

BRANCH III - PHYSICS FIFTH SEMESTER

			REG. No				
	CR : ELEC	OR – CORE CTRONICS INS.	MA	X. MARKS : 30			
		SECTION	- A				
TO BE ANSWERED IN THE QUESTION PAPER ITSELF							
	ANSWER ALL QU	JESTIONS:		$(30 \times 1 = 30)$			
I	CHOOSE THE CO	RRECT ANSWER:					
1.	In a common base c a) 1.95	onnection 1 _E =1mA as b) 0.95	nd l_C =0.95mA. The c) 0.05	e value of I_B is d) 0.90			
2.	In a common base c a) 0.05	onnection 1_C =0.95mA b) 1.0	and $I_E = 1$ mA. Th c) 1.95	the value of α is d) 0.95			
3.	The Collector of a N a) intrinsic c) heavily doped	IPN Transistor is	b) lightly doped d) moderately dop	oed			
4.	We have β as given a) $1/1-\alpha$	•	c) 1/1+α	d) $\alpha/1+\alpha$			
5.	If $\alpha = 0.98$, the value a) 98	e of β is as given below by 50	ow c) 49	d) 0.02			
6.	If the value of $\beta = 50$ a) 1mA	0; and $1_B = 20 \mu$, the b) 1.2mA	_				
7.	-	etion of a dc and ac lo b) Cut-off point		t d) Firing point			
8.	In a RC coupled vol a) increasing	tage amplifier, the vo	ltage gain over mid c) constant	frequency range is d) erratic			
9.	Stabilization makes a) independent	the Operating point, b) dependent	c) constant	d) compensated			

10.	For Voltage amplification, a Transistor in junction a) forward biased b) reverse biased					
11.	Thermal runway is caused mainly by a) base current c) collector leakage current	b) collector current d) $I_{\rm E}$				
12.	Negative resistance behavior is experien a) JFET b) MOSFET					
13.	In general a MOSFET can function in the following mode of operation, a) depletion only b) enhancement only c) both depletion & enhanced modes d) none					
14.	No. of Flip flops required to store a deci a) 4 b) 8	imal number 2008 in a binary register is c) 10 d) 11				
15.	CMRR serves as a figure of merit of a a) voltage amplifier c) difference amplifier	b) power amplifierd) current amplifier				
II	FILL IN THE BLANKS:					
16.	In a RC coupled amplifier the Capacitor connected in to the emitter Resistance in the self bias arrangement is called the by-pass capacitor.					
17.	UJT fires when its emitter junction is biased.					
18.	The Gate-Source junction of a JFET is always biased.					
19.	The sum of Products form leads to network.					
20.	In closed loop application of OPAMP, the voltage at its two input terminals are					
III	STATE TRUE OR FALSE:					
21.	JFET is a bi-polar device.					
22.	DC load line is steeper the AC load line.					
23.	Thermal runway in encountered in FET also.					
24.	NOR gate is one of the basic gates.					
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- 26. Draw the circuit to get an OR function using NAND gate.
- 27. What happens to the content of a register after performing Left Shift operation Thrice?
- 28. Why is base of a transistor made thin?
- 29. Draw the circuit of a unity gain non-inverting amplifier using OP AMP.
- 30. Define Intrinsic stand-off ratio of a UJT.



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COURSE : **MAJOR – CORE** PAPER : **ELECTRONICS**

TIME : **2** ½ **HOURS** MAX. MARKS : 70

SECTION - B

ANSWER ANY FIVE QUESTIONS:

 $(5 \times 5 = 25)$

- 1. A Transistor is connected in common emitter (CE) configuration in which collector supply is 9V and the voltage drop across resistance R_C connected in the collector circuit is 0.98V. The value of $R_C = 1 \text{K}\Omega$. If $\alpha = 0.98$ determine: i) the collector-emitter voltage (V_{CE}) (ii) the base current (I_B).
- 2. Calculate the emitter current in the voltage divider circuit with the following values. $R_1 = 10 K\Omega$ $R_2 = 10 K\Omega$ $R_C = 1 K\Omega$ $R_E = 5 K\Omega$ $V_{CC} = 20 V$. Also find the value of V_{CE} and collector potential V_C .
- 3. The following readings were obtained experimentally for a JFET: V_{GS} =0V and when V_{DS} =7V, I_{D} =10mA; when V_{GS} =0V and V_{DS} =15V, I_{D} =10.25mA and when V_{GS} =0.2V & V_{DS} =15V, I_{D} =9.65mA. Determine: i) ac drain resistance ii) transconductance and iii) amplification factor.
- 4. The intrinsic stand-off ratio η for a UJT=0.6. If the inter-base resistane is $10k\Omega$, what are the values of R_{B1} and R_{B2} ?
- 5. SIMPLIFY the logic function using K-Map and realize the logic circuit using NAND gates. $F(ABCD) = \Sigma m (1,3,7,11,15)$ and don't care d(0,2,5).
- 6. Implement (i) EX-OR function using NOR gates. (ii) NOT function using EX-OR gate.
- Using OpAmp IC 741, draw the Analog circuit for the following:
 i) An Inverting Amplifier having a gain of 20 with an input impedance of 10K Ω. ii) a Non-Inverting Amplifier with a gain of +20.

SECTION - C

ANSWER ANY THREE QUESTIONS:

 $(3 \times 15 = 45)$

8. Explain with diagram the functioning at a R-C coupled transistor amplifier with special reference to its frequency response behaviour.

PH/MC/ES54

- 9. Account for the formation of wedge shaped depletion regions and the channel construction of a JFET.

 Explain the mechanism of current flow in a enhancement mode MOSFET.
- 10. Implement a 4-Bit Parallel Binary Adder/Subtractor circuit using Full Adders & Ex-OR gates. Explain the functioning of the Circuit with a suitable example.
- 11. Draw the logic circuit and explain the functioning of the following counters.i) MOD 5 Ripple Counter ii) Left Shift Register.
- 12. Using OpAmp draw the circuit and explain the working of the following:
 - i) Adder ii) subtractor
- iii) Inverter
- iv) Integrator

v) Differentiator

